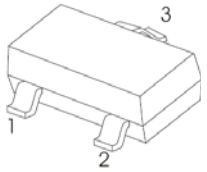
N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (mΩ)	I_D (mA)
60	2.8 at V_{GS} = 10 V	250

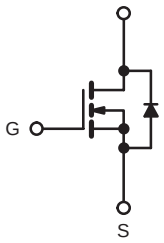
SOT－23



1. GATE
2. SOURCE
3. DRAIN

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Low Threshold: 2 V (typ.)
- Low Input Capacitance: 25 pF
- Fast Switching Speed: 25 ns
- Low Input and Output Leakage
- TrenchFET® Power MOSFET
- 1200V ESD Protection
- Compliant to RoHS Directive 2002/95/EC



N-Channel MOSFET

BENEFITS

- Low Offset Voltage
- Low-Voltage Operation
- Easily Driven Without Buffer
- High-Speed Circuits
- Low Error Voltage

APPLICATIONS

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)[b]	T_A = 25 °C	I_D	250	mA
	T_A = 100 °C		150	
Pulsed Drain Current[a]		I_{DM}	800	
Power Dissipation[b]	T_A = 25 °C	P_D	0.30	W
	T_A = 100 °C		0.13	
Maximum Junction-to-Ambient[b]		R_{thJA}	350	°C/W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

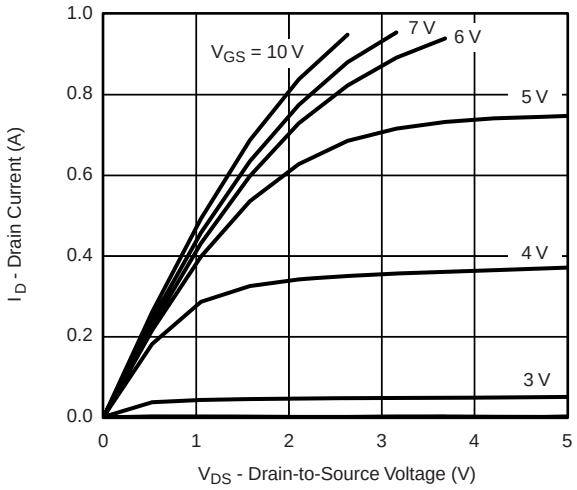
Notes:
a. Pulse width limited by maximum junction temperature.
b. Surface Mounted on FR4 board.

SPECIFICATIONS T_A = 25 °C, unless otherwise noted

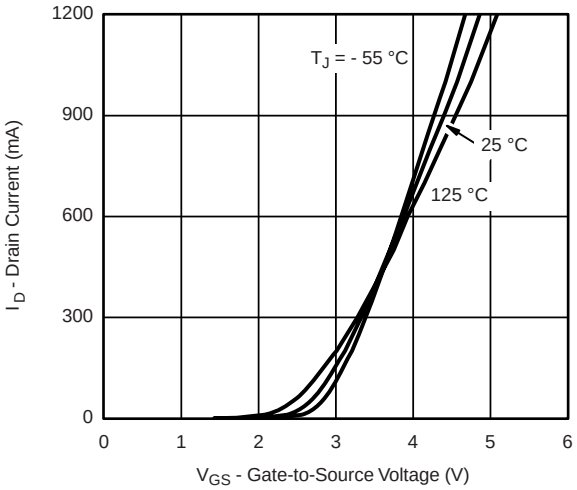
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.[a]	Max.	
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 10 µA	60			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1		2.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 10	µA
		V_{DS} = 0 V, V_{GS} = ± 15 V			1	
		V_{DS} = 0 V, V_{GS} = ± 10 V			± 150	nA
		V_{DS} = 0 V, V_{GS} = ± 10 V, T_J = 85 °C			± 1000	
		V_{DS} = 0 V, V_{GS} = ± 5 V			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V			1	µA
		V_{DS} = 60 V, V_{GS} = 0 V , T_J = 125 °C			500	
On-State Drain Current[a]	$I_{D(on)}$	V_{GS} = 10 V, V_{DS} = 7.5 V	500			mA
		V_{GS} = 4.5 V, V_{DS} = 10 V	300			
Drain-Source On-Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 200 mA		2800	3300	mΩ
		V_{GS} = 4.5 V, I_D = 150 mA		3100	3800	
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 100 mA	100			mS
Diode Forward Voltage	V_{SD}	I_S = 100 mA, V_{GS} = 0 V			1.3	V
Dynamic[a]						
Total Gate Charge	Q_g	V_{DS} = 10 V, V_{GS} = 4.5 V $I_D \cong$ 150 mA		0.4	0.6	nC
Input Capacitance	C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V f = 1 MHz		25		pF
Output Capacitance	C_{oss}			5		
Reverse Transfer Capacitance	C_{rss}			2.0		
Switching[a, b, c]						
Turn-On Time	$t_{d(on)}$	V_{DD} = 30 V, R_L = 150 Ω $I_D \cong$ 200 mA, V_{GEN} = 10 V, R_G = 10 Ω			20	ns
Turn-Off Time	$t_{d(off)}$				30	

Notes:
a. For DESIGN AID ONLY, not subject to production testing.
b. Pulse test: PW ≤ 300 µs duty cycle ≤ 2 %.
c. Switching time is essentially independent of operating temperature.

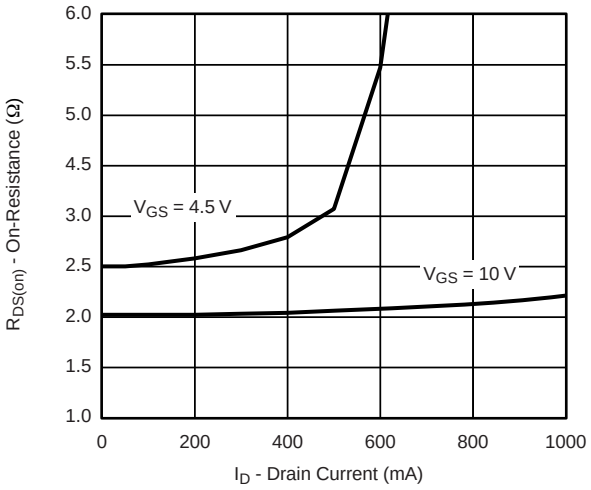
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



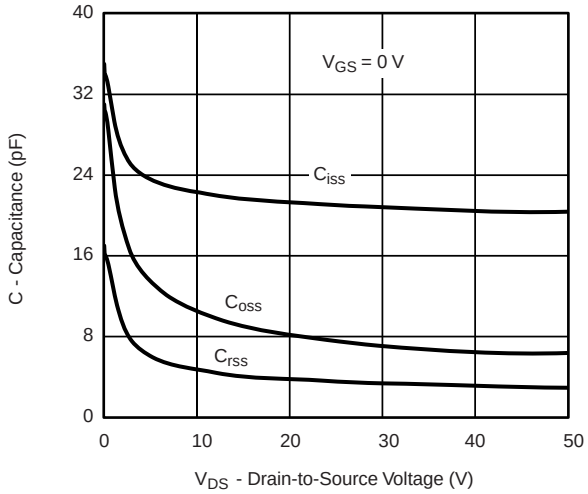
Output Characteristics



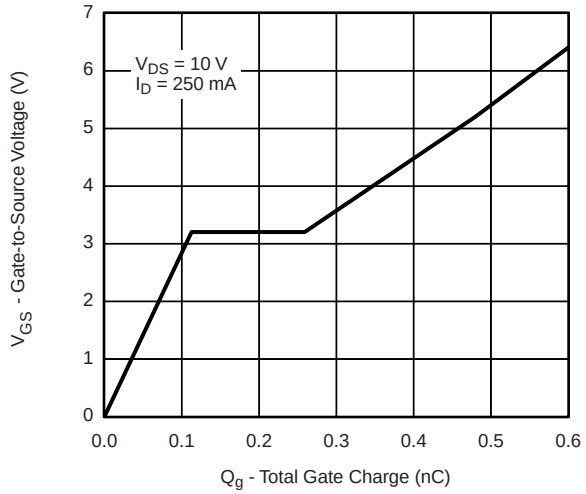
Transfer Characteristics



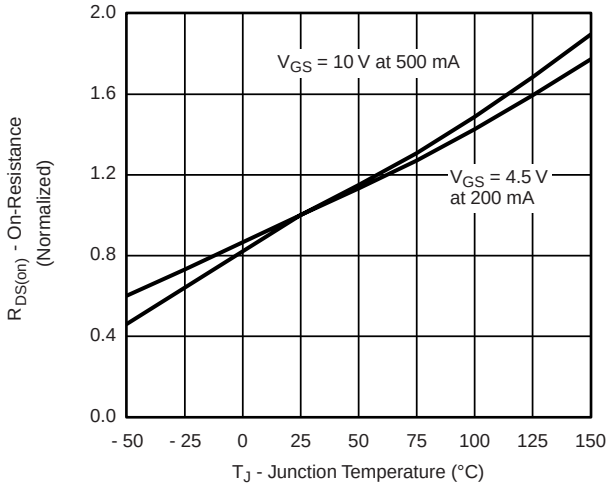
On-Resistance vs. Drain Current



Capacitance

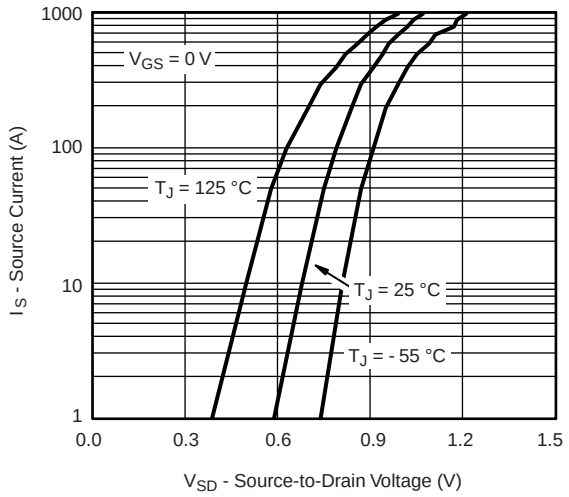


Gate Charge

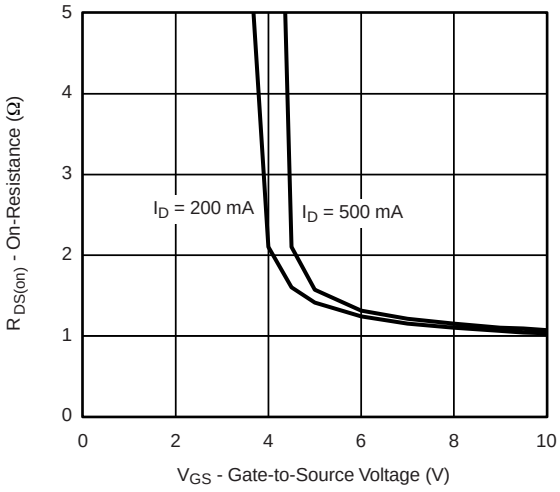


On-Resistance vs. Junction Temperature

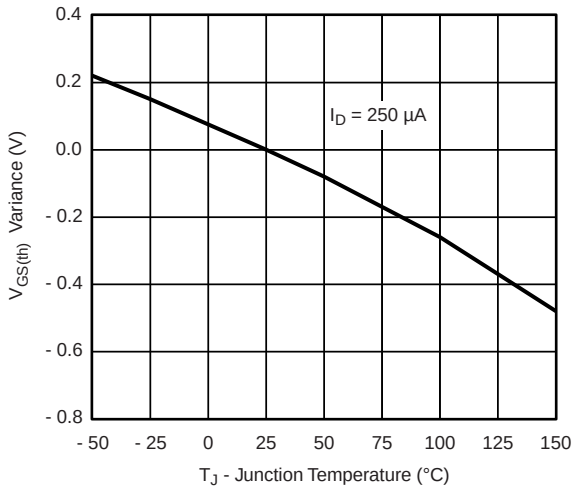
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



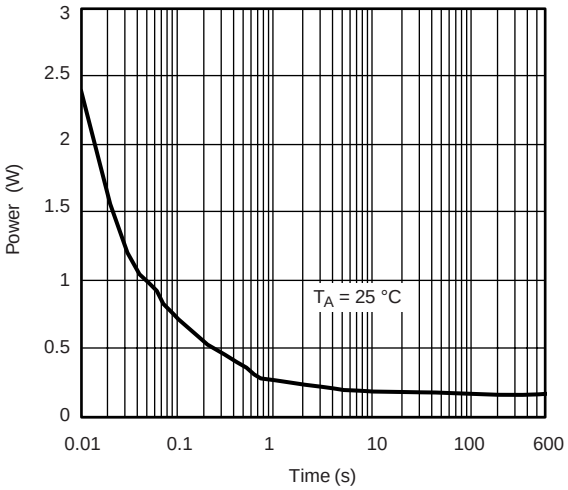
Source-Drain Diode Forward Voltage



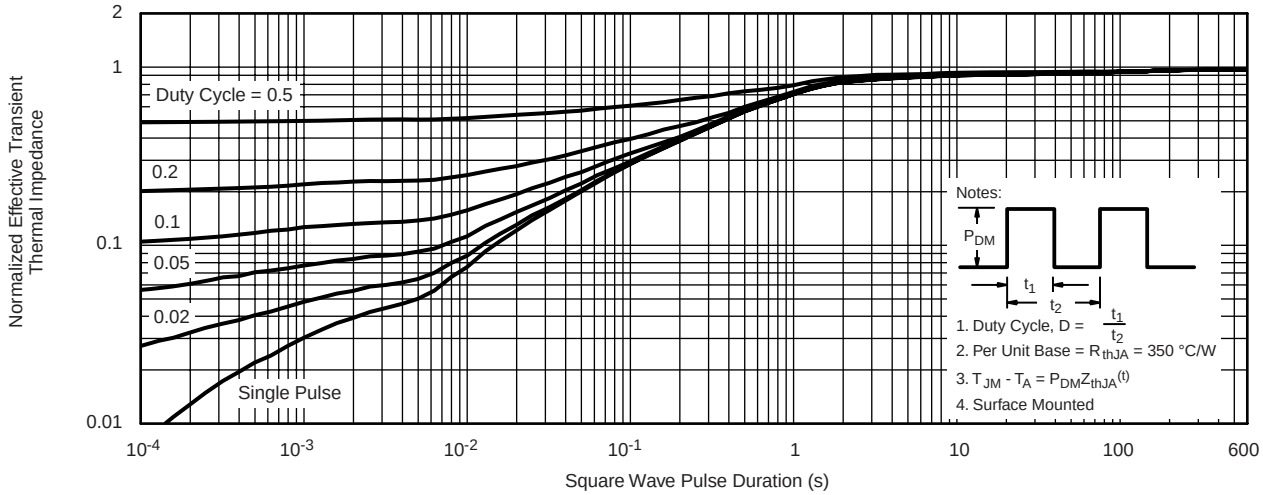
On-Resistance vs. Gate-Source Voltage



Threshold Voltage Variance Over Temperature

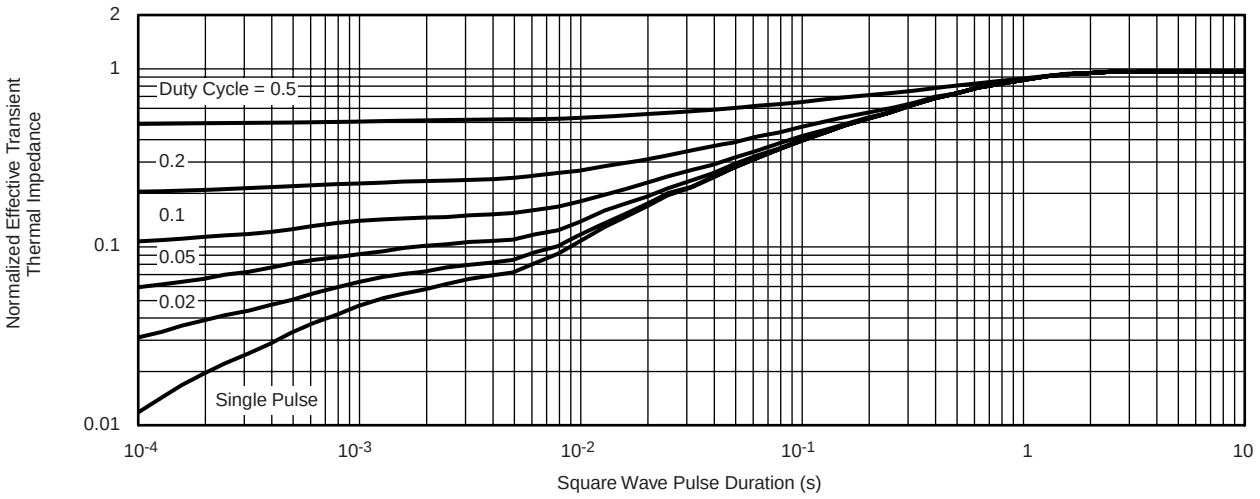


Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



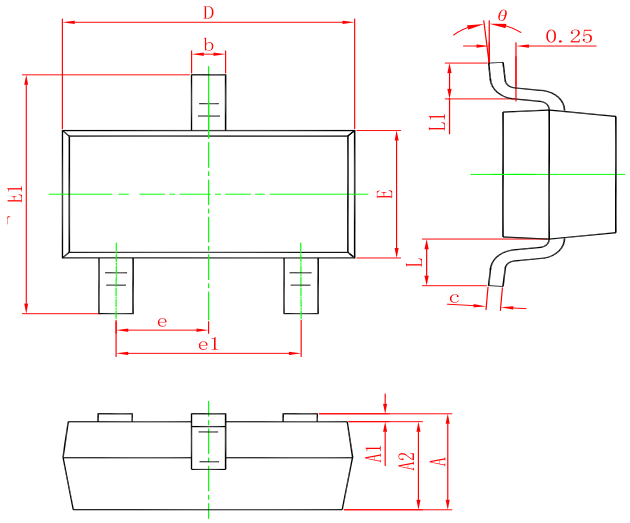
Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 ℃)

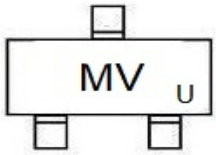
  are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW BS170FTA	SOT-23	3000	Tape and reel